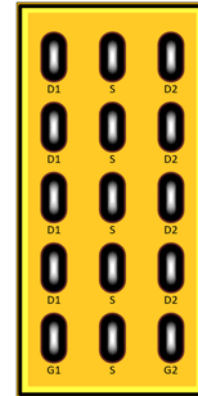
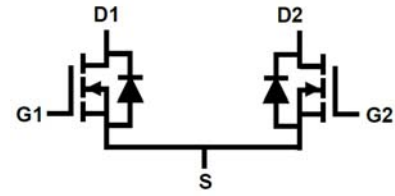


General Description

- Ultra High Switching Frequency
- Ultra Low $R_{DS(on)}$
- Fast and Controllable Fall and Rise Time
- Zero Reverse Recovery Loss
- Dual Channels, Common Source
- Protective Backside Coating

Applications

- Point of Load Converters
- Lidar Application
- Class-D Audio
- Envelope Tracking Power Supplies
- Pulsed Power Applications



Package: WLCSP 5X3

Size: 1.58mmX3.58mm

Maximum Ratings (Q1 & Q2)

Symbol	Parameter	Max	Unit
V_{DS}	Drain-to-Source Voltage (Continuous)	100	V
I_D	Continuous Current	7	A
	Pulsed (25°C , $T_{Pulse} = 100 \mu\text{s}$)	90	A
V_{GS}	Gate-to-Source Voltage	6	V
	Gate-to-Source Voltage	-4	V
T_J	Operating Temperature	-40 to 150	$^{\circ}\text{C}$
T_{STG}	Storage Temperature	-40 to 150	$^{\circ}\text{C}$

Electrical Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise stated) (Q1 & Q2)

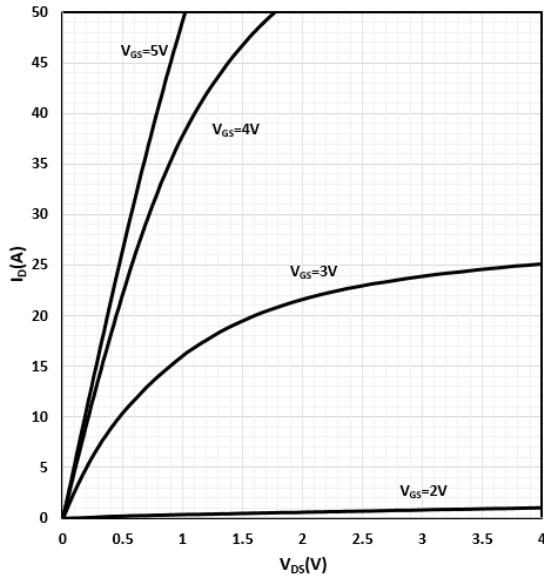
Symbol	Parameter	Min	Typ.	Max	Unit	Test Condition
Static Parameters						
BV_{DSS}	Drain-to-Source Voltage	100			V	$V_{GS} = 0\text{ V}, I_D = 120\mu\text{A}$
I_{DSS}	Drain Source Leakage		20	80	μA	$V_{GS} = 0\text{ V}, V_{DS} = 80\text{V}$
I_{GSS}	Gate-to-Source Forward Leakage		0.1	1	mA	$V_{GS} = 5\text{ V}$
	Gate-to-Source Reverse Leakage		20	80	μA	$V_{GS} = -4\text{ V}$
$V_{GS(TH)}$	Gate Threshold Voltage	0.8	1.3	2.4	V	$V_{DS} = V_{GS}, I_D = 1.9\text{mA}$
$R_{DS(on)}$	Drain-Source On Resistance		19	25	m Ω	$V_{GS} = 5\text{ V}, I_D = 7\text{A}$
V_{SD}	Source-Drain Forward Voltage		1.9		V	$I_S = 0.8\text{ A}, V_{GS} = 0\text{ V}$
Dynamic Parameters						
C_{iss}	Input Capacitance		307	384	pF	$V_{GS} = 0\text{ V}, V_{DS} = 50\text{V}$
C_{oss}	Output Capacitance		150	218		$V_{GS} = 0\text{ V}, V_{DS} = 50\text{V}$
C_{rss}	Reverse Transfer Capacitance		1.8	2.5		$V_{GS} = 0\text{ V}, V_{DS} = 50\text{V}$
$C_{oss(er)}$	Energy Related Coss		196			$V_{GS} = 0\text{ V}, V_{DS} = 50\text{V}$
$C_{oss(tr)}$	Time Related Coss		264			$V_{GS} = 0\text{ V}, V_{DS} = 50\text{V}$
R_G	Gate Resistance		900		m Ω	
Q_G	Total Gate Charge		2.75	3.45	nC	$V_{GS} = 5\text{V}, V_{DS} = 50\text{V}, I_D = 7\text{A}$
Q_{GS}	Gate to Source Charge		0.65			$V_{DS} = 50\text{V}, I_D = 7\text{A}$
Q_{GD}	Gate to Drain Charge		0.50	1.00		$V_{DS} = 50\text{V}, I_D = 7\text{A}$
$Q_{G(TH)}$	Gate Charge at Threshold		0.40			$V_{DS} = 50\text{V}, I_D = 7\text{A}$
Q_{OSS}	Output Charge		13.5	18.5		$V_{DS} = 50\text{V}, I_D = 7\text{A}$

Thermal Parameters

Symbol	Parameter	Typ	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case	0.5	$^\circ\text{C/W}$
$R_{\theta JB}$	Thermal Resistance, Junction to Board	5.0	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1)	62	$^\circ\text{C/W}$

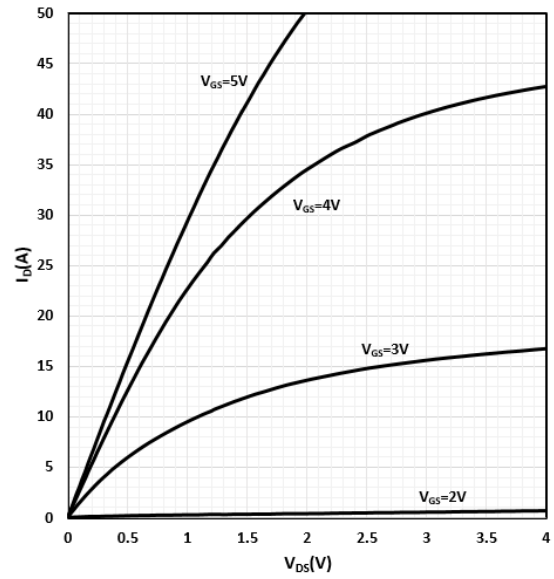
Note 1: $R_{\theta JA}$ is determined with the device mounted on one square inch of copper pad, single layer 2 oz copper on FR4 board.

Fig1 Typ. Output Characteristics (Q1 & Q2)



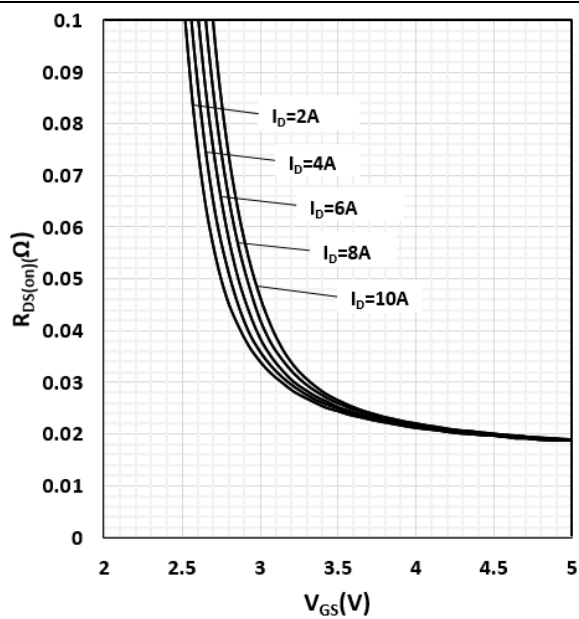
$I_D = f(V_{DS}, V_{GS}); T_J = 25^\circ\text{C}$

Fig2 Typ. Output Characteristics (Q1 & Q2)



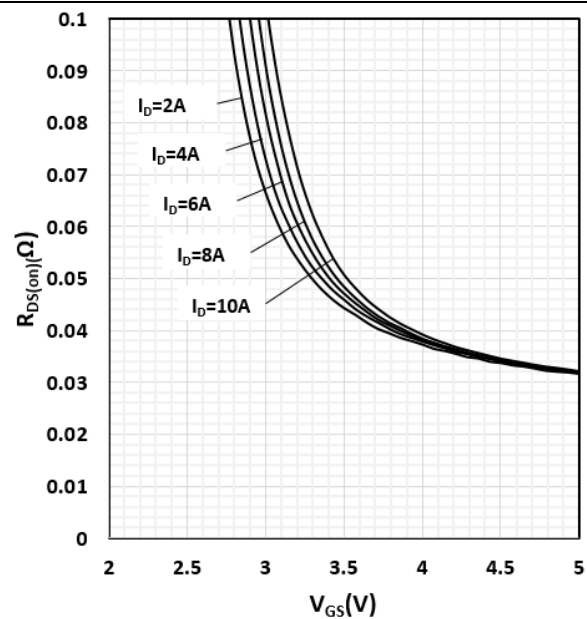
$I_D = f(V_{DS}, V_{GS}); T_J = 125^\circ\text{C}$

Fig3 Typ. Drain-Source On Resistance (Q1 & Q2)



$R_{DS(on)} = f(I_D, V_{GS}); T_J = 25^\circ\text{C}$

Fig4 Typ. Drain-Source On Resistance (Q1 & Q2)



$R_{DS(on)} = f(I_D, V_{GS}); T_J = 125^\circ\text{C}$

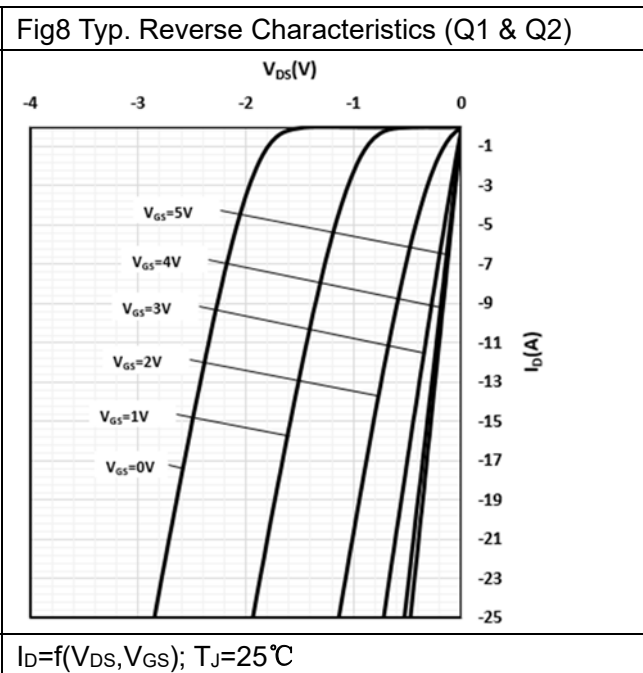
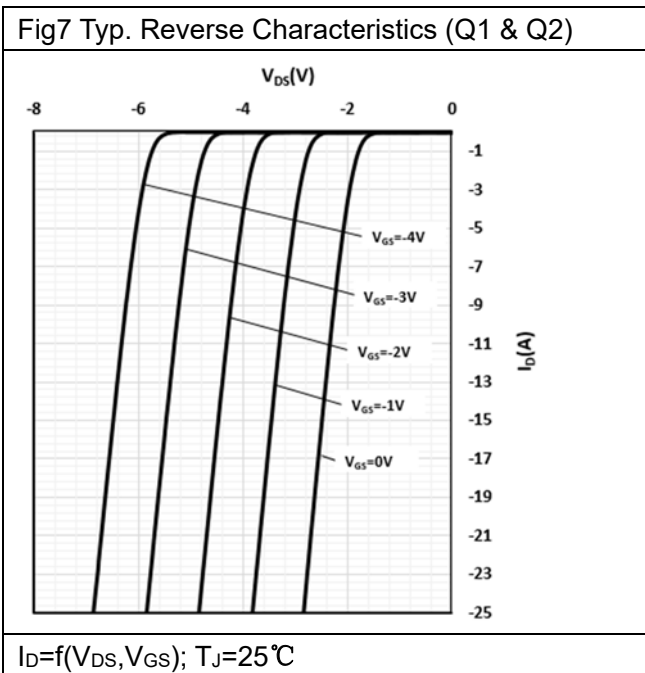
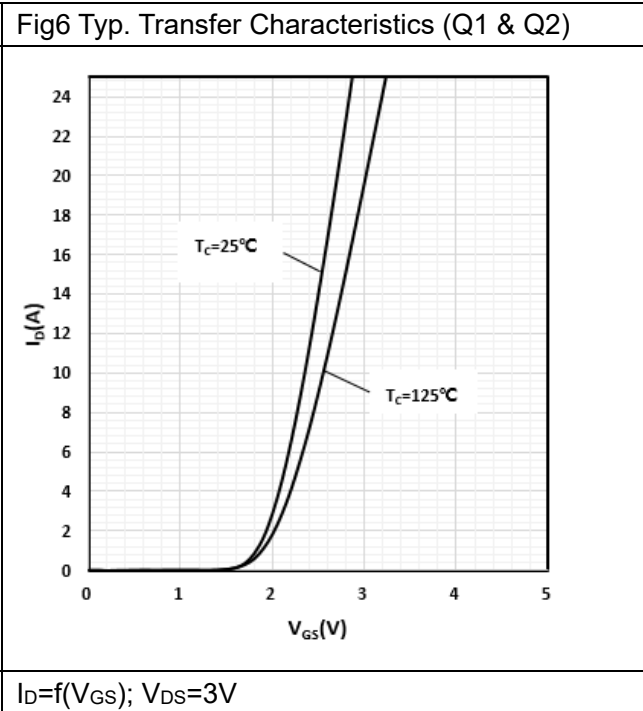
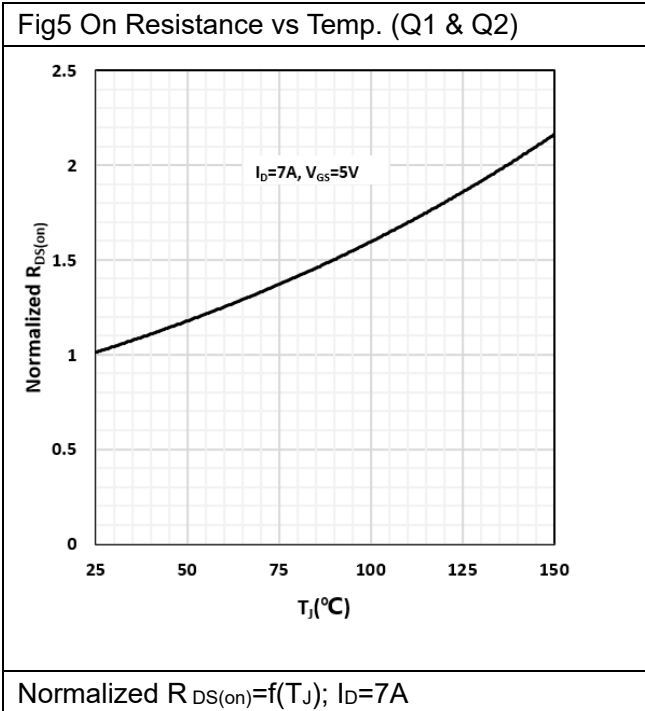
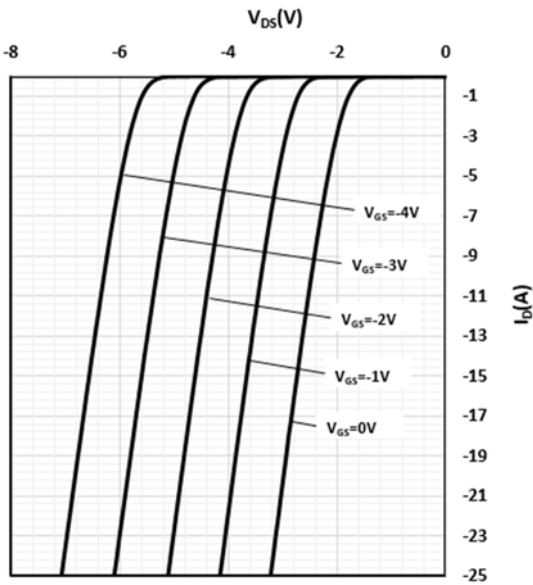
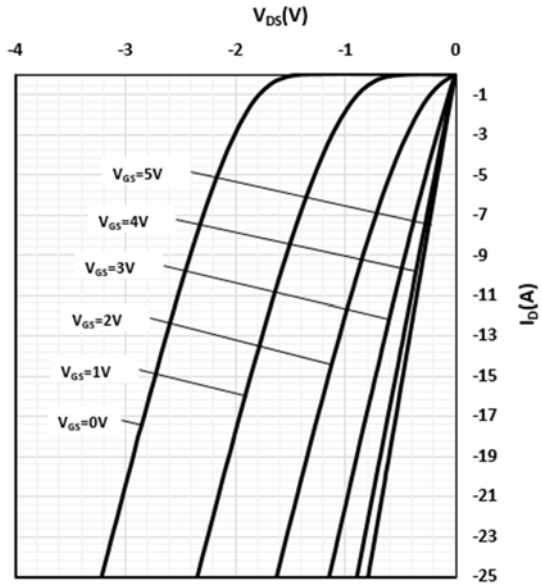


Fig9 Typ. Reverse Characteristics (Q1 & Q2)



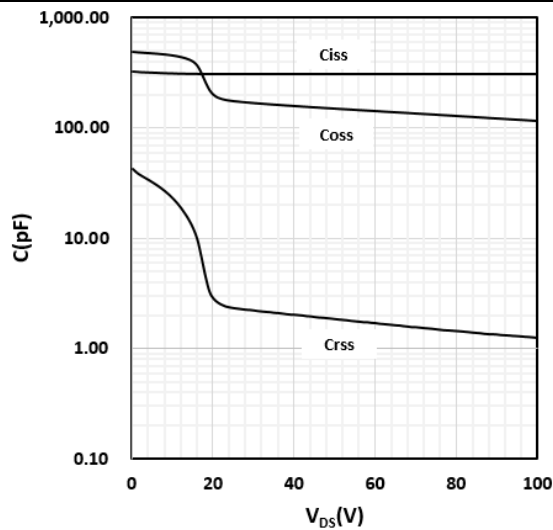
$I_D = f(V_{DS}, V_{GS}); T_J = 125^\circ\text{C}$

Fig10 Typ. Reverse Characteristics (Q1 & Q2)



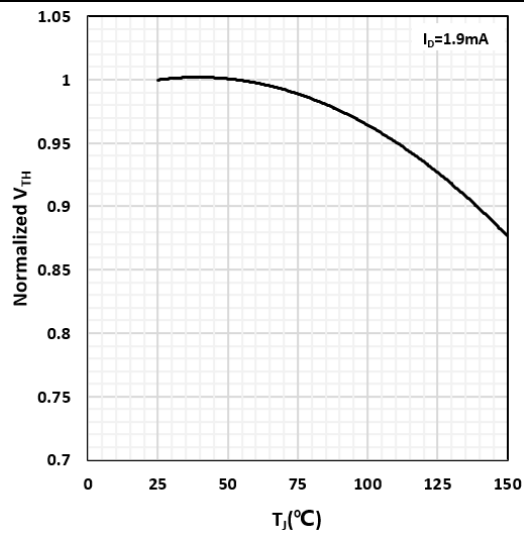
$I_D = f(V_{DS}, V_{GS}); T_J = 125^\circ\text{C}$

Fig11 Typ. Capacitances (Q1 & Q2)



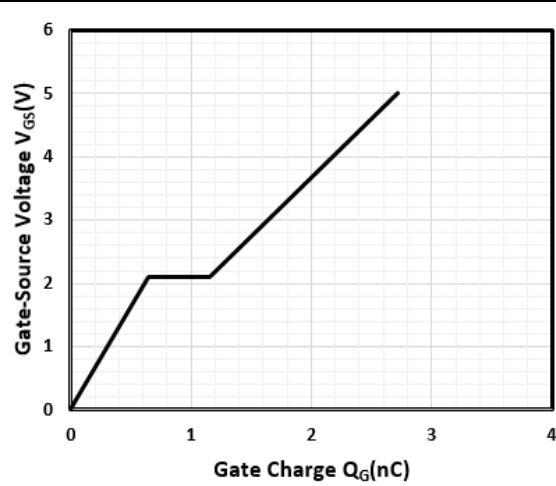
$C_{XSS} = f(V_{DS}); f = 100\text{KHz}$

Fig12 Threshold Voltage vs Temp. (Q1 & Q2)



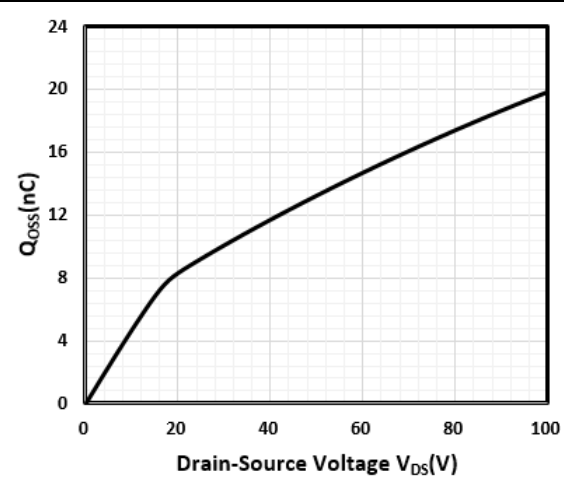
$V_{TH} = f(T_J); V_{GS} = V_{DS}; I_D = 1.9\text{mA}$

Fig13 Typ. Gate Charge (Q1 & Q2)



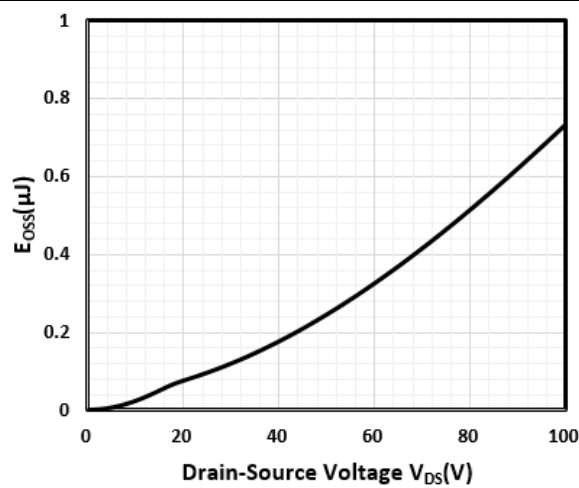
$V_{GS} = f(Q_G)$; $V_{DCLINK} = 50V$; $I_D = 7A$

Fig14 Output Charge (Q1 & Q2)



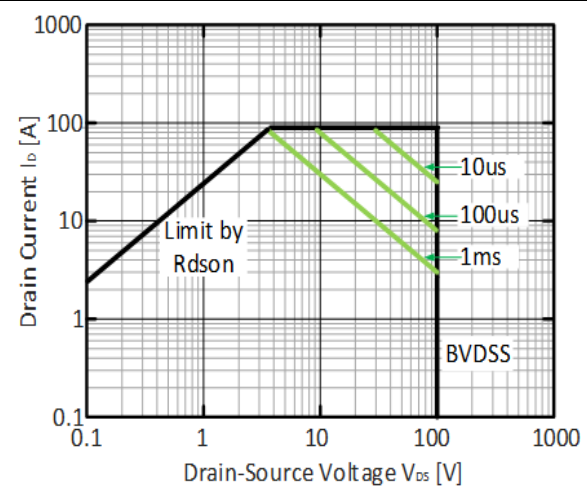
$Q_{oss} = f(V_{DS})$

Fig15 Output Capa. Stored Energy (Q1 & Q2)



$E_{oss} = f(V_{DS})$

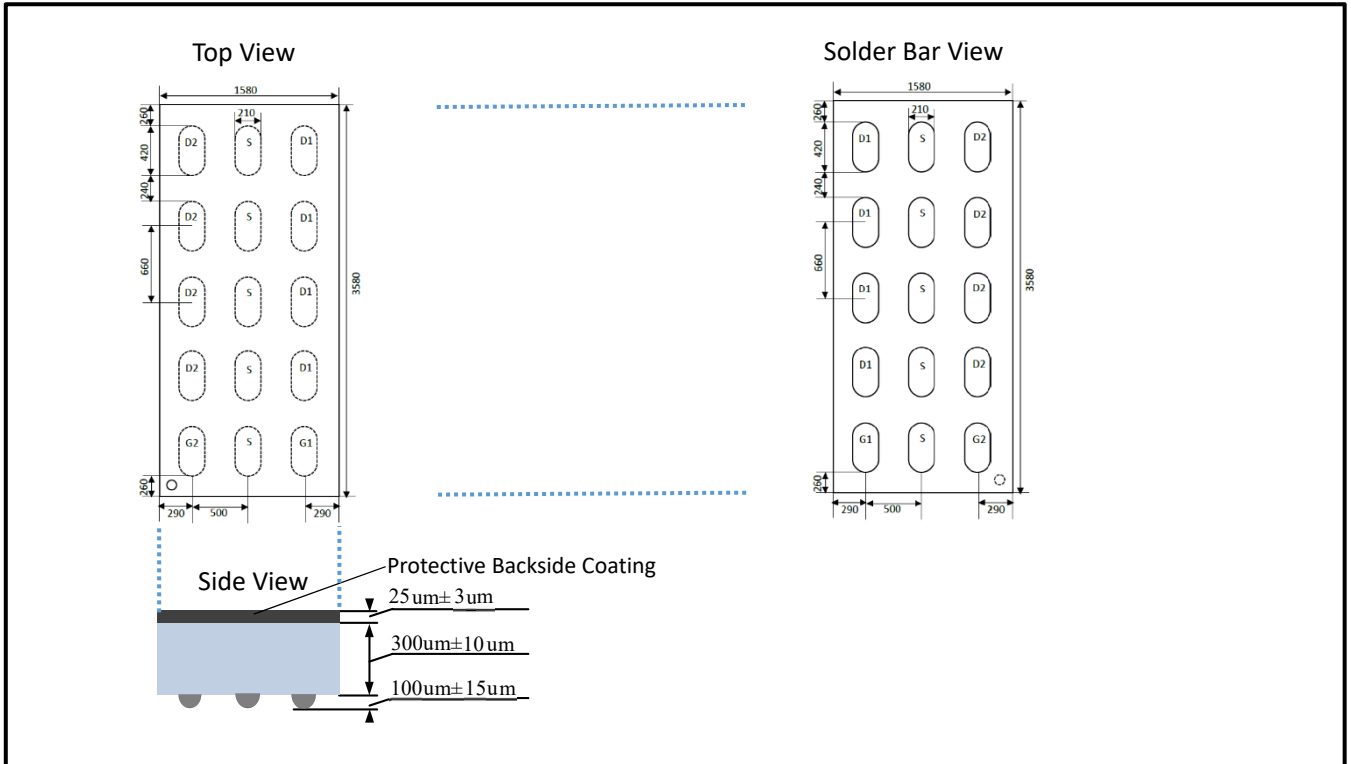
Fig16 Safe Operating Area (Q1 & Q2)



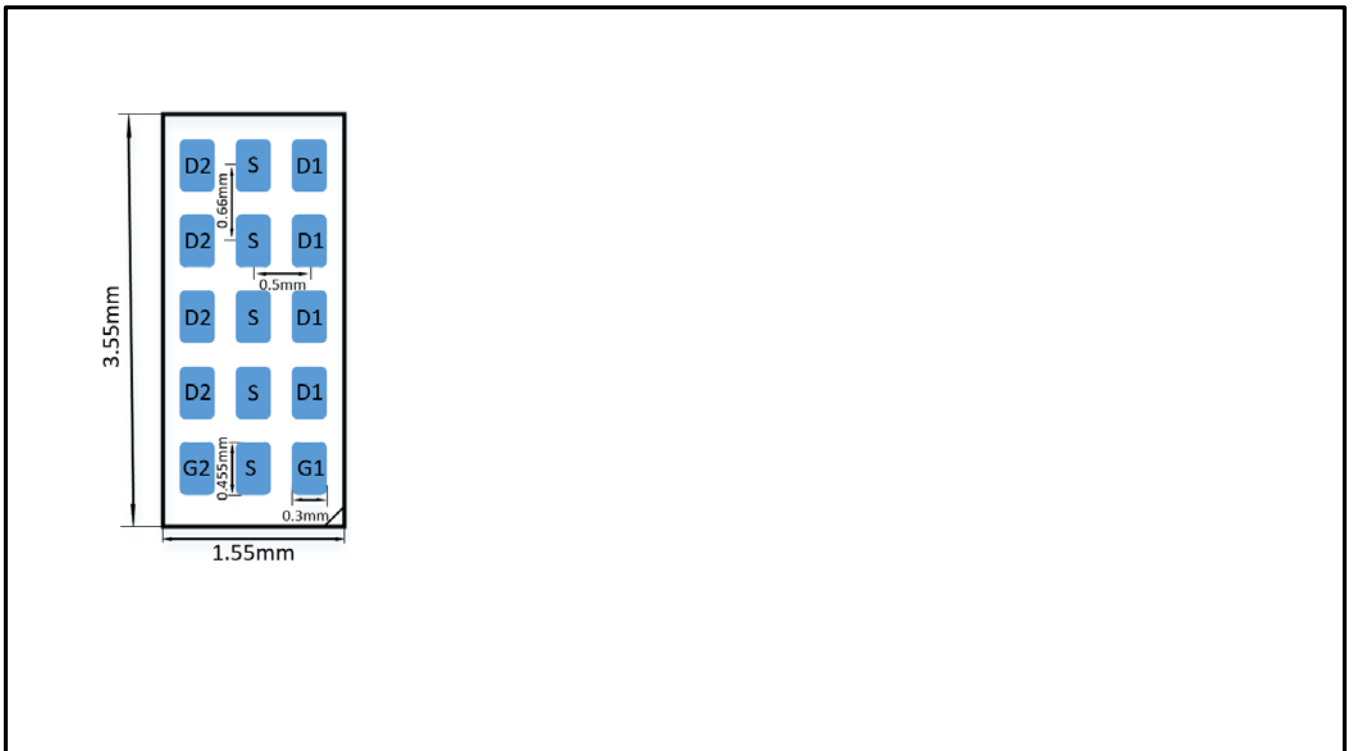
$I_D = f(V_{DS})$; $T_C = 25^\circ C$; parameter: t_p

<p>Fig17 Power Dissipation</p> <p>Power_{total} [W]</p> <p>Temperature T_{case} [°C]</p>	<p>Fig18 Max. Transient Thermal Impedance</p> <p>Z_{thJC} [°C/W]</p> <p>Rectangular Pulse Duration [s]</p> <p>Duty=</p> <ul style="list-style-type: none"> 0.5 0.2 0.1 0.05 0.02 0.01 <p>Single Pulse</p>
<p>$P_{tot}=f(T_{case})$</p>	<p>$Z_{thJC} = f(t_p)$; parameter: $D= t_p / T$</p>

Package Reference



Recommended PCB Layout



Marking Reference



Gate Position

Marking Line 1	Company Code
Marking Line 2	Device Code
Marking Line 3	Lot/ Package Code
Marking Line 4	Lot/ Package Code

Reel Reference

